

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	2	"6643165".pn.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	4	lu near hongqiang.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	8	barth near william.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	133	burke near peter.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	0	4 and nanotube	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	0	4 and nano-tube	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	2083	438/257.ccls.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	2	7 and nanotube near layer	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	17	(nanotube near layer) near35 (chamber)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	2	((nanotube near layer) near35 (chamber)) near35 (silicon)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	9	((nanotube) near35 (chamber)) near35 (silicon)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	0	((nano-tube) near35 (chamber)) near35 (silicon)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	1	((nano near tube) near35 (chamber)) near35 (silicon)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	57	((nano near tube)) near35 (silicon)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	26	((nano-tube)) near35 (silicon)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	819	((nanotube)) near35 (silicon)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
17	BRS	L17	263	((nanotube)) near35 (silicon)) near45 (substrate)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
18	BRS	L18	57	((nanotube)) near35 (silicon)) near45 (contact)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
19	BRS	L19	164	((nano\$5)) near35 (silicon)) near45 (contact)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
20	BRS	L20	388	((nano\$5)) near35 (silicon)) near45 (silicon near nitride or sin)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
21	BRS	L21	111	((nanotube)) near35 (silicon)) near45 (silicon near nitride or si)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
22	BRS	L22	111	((nanotube)) near35 (silicon)) near45 ((silicon near nitride) or (si))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
23	BRS	L23	4	(nanotube) near35 (silicon near5 chamber)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
24	BRS	L24	819	(nanotube) near35 (silicon)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
25	BRS	L25	897	(dielectric or insulat\$3) near35 (silicon near5 chamber)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
26	BRS	L26	17	((dielectric or insulat\$3) near35 (silicon near5 chamber)) near35 (contact near hole\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
27	BRS	L27	10	((nano\$5)) near35 (silicon)) near45 (contact near hole\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
28	BRS	L28	0	((nanotube)) near35 (silicon)) near45 (contact near hole\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
29	BRS	L29	66	((nanotube)) near35 (silicon)) near45 (contact or hole\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B



	U	1	Document ID	Title
1			US 20050067693 A1	Semiconductor device and manufacturing method thereof
2			US 20050058797 A1	High purity nanotube fabrics and films
3			US 20050058590 A1	Spin-coatable liquid for formation of high purity nanotube films
4			US 20050036933 A1	Carbide nanofibrils and method of making same
5			US 20030172726 A1	Scanning probe microscope for ultra sensitive electro-magnetic field detection and probe thereof
6			US 20020102353 A1	Method of producing a nanotube layer on a substrate
7			US 6817231 B2	Scanning probe microscope for ultra sensitive electro-magnetic field detection and probe thereof
8			US 6157043 A	Solenoid comprising a compound nanotube and magnetic generating apparatus using the compound nanotube
9			WO 9630570 A1	CARBIDE NANOFIBRILS AND METHOD OF MAKING SAME